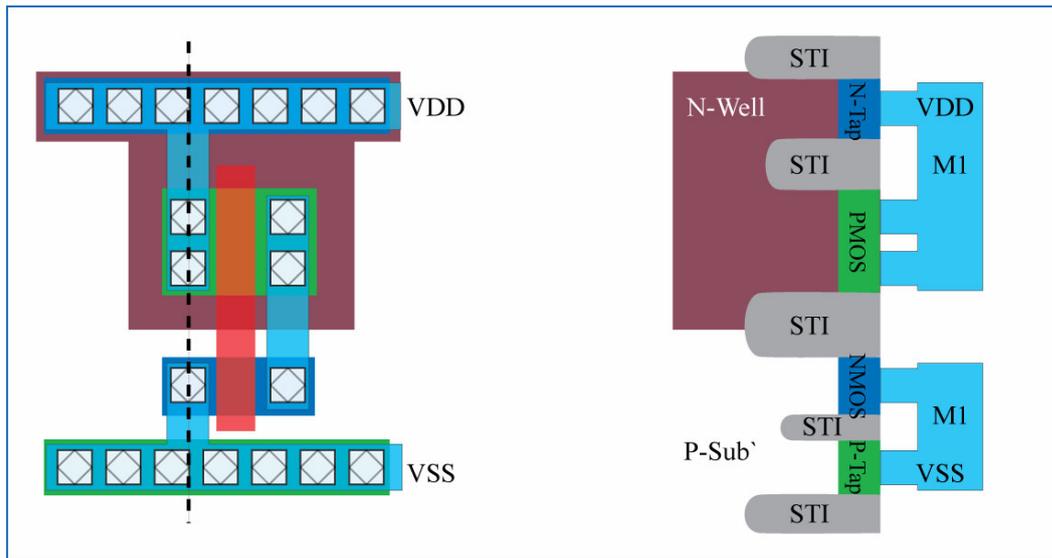


Without looking at the cross-section on the right, study the layout for a moment. Can you spot the problem in the layout? Now, study the cross-section of the layout along the dotted line. Can you see that the n-tap and the p-tap are isolated on four sides by the isolation oxide and hence are electrically far away from the transistors?



Two alternative layouts are shown below. The p-tap is butted with the n-diffusion, and the n-tap is butted with the p-diffusion. The trade-off in the new layouts is a larger area.

